



SANYO Semiconductors

## DATA SHEET

# 2SK2628LS

N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- Low Qg.
- Ultrahigh-speed switching.

### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		600	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±30	V
Drain Current (DC)	I <sub>D</sub>		6	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	24	A
Allowable Power Dissipation	P <sub>D</sub>		2.0	W
		Tc=25°C	35	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E <sub>AS</sub>		98	mJ
Avalanche Current *2	I <sub>AV</sub>		6	A

\*1 V<sub>DD</sub>=50V, L=5mH, I<sub>AV</sub>=6A

\*2 L≤5mH, single pulse

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	600			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V			1.0	mA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V			±100	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	3.5		5.5	V

Marking : K2628

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**SANYO Semiconductor Co., Ltd.**

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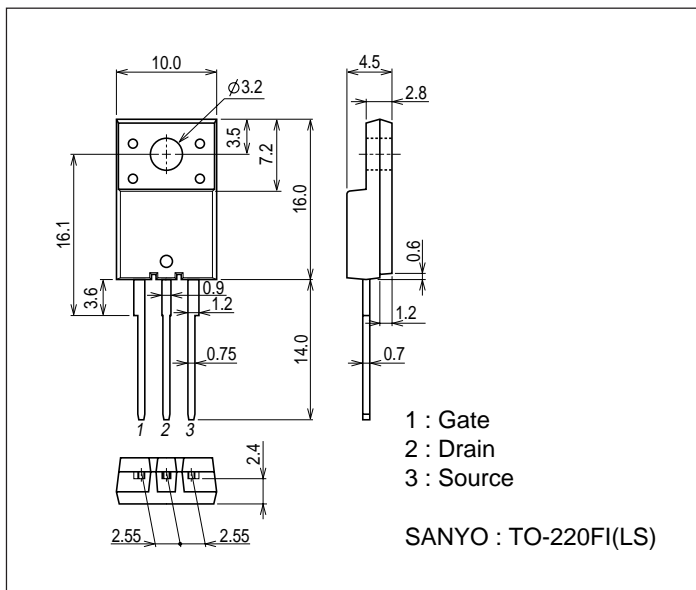
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=4A$	2.0	4.0		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=2A, V_{GS}=15V$		0.9	1.1	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=20V, f=1MHz$		1050		pF
Output Capacitance	$C_{oss}$	$V_{DS}=20V, f=1MHz$		320		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=20V, f=1MHz$		180		pF
Total Gate Charge	$Q_g$	$V_{DS}=200V, I_D=6A, V_{GS}=10V$		30		nC
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		23		ns
Rise Time	$t_r$	See specified Test Circuit.		35		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		90		ns
Fall Time	$t_f$	See specified Test Circuit.		35		ns
Diode Forward Voltage	$V_{SD}$	$I_S=6A, V_{GS}=0V$		0.85	1.2	V

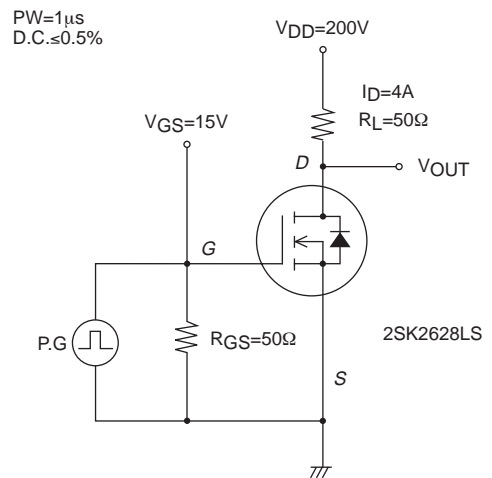
**Package Dimensions**

unit : mm (typ)

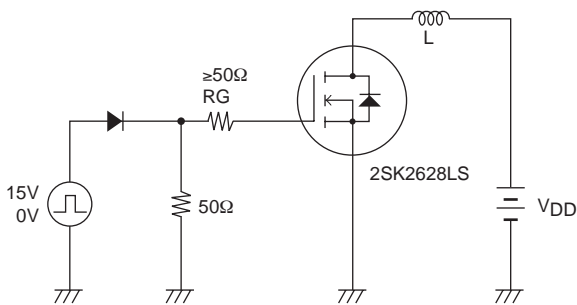
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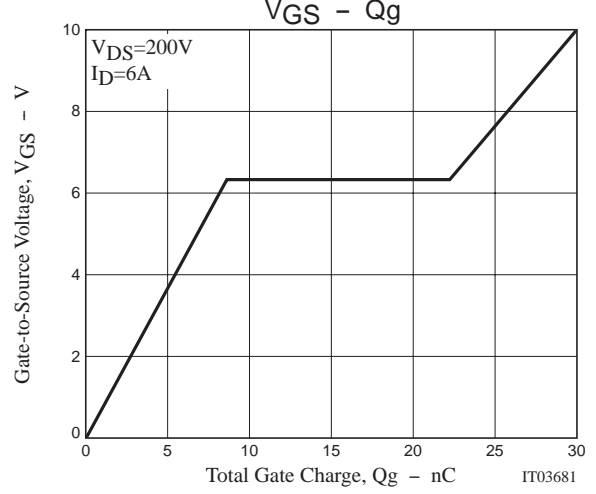
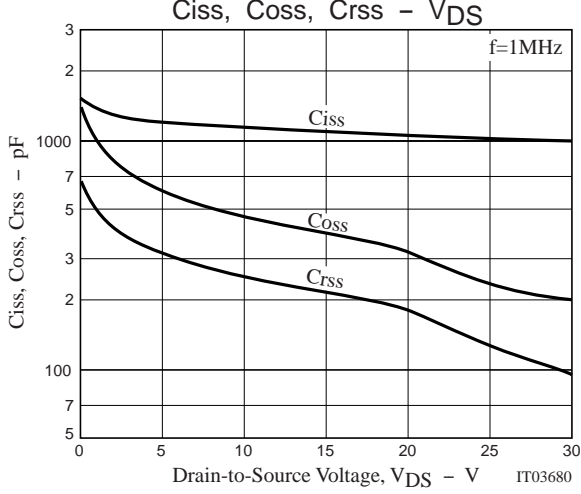
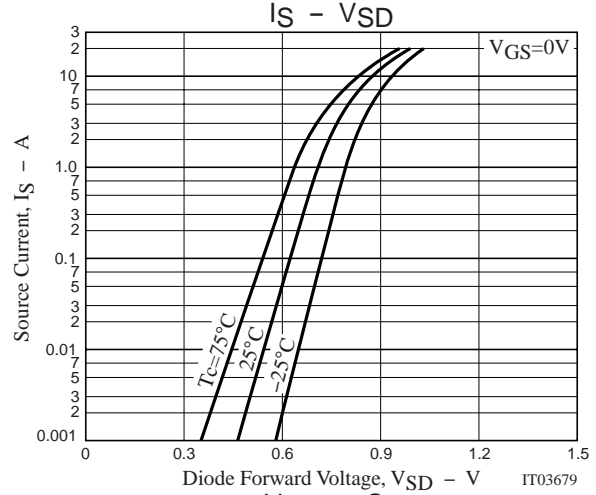
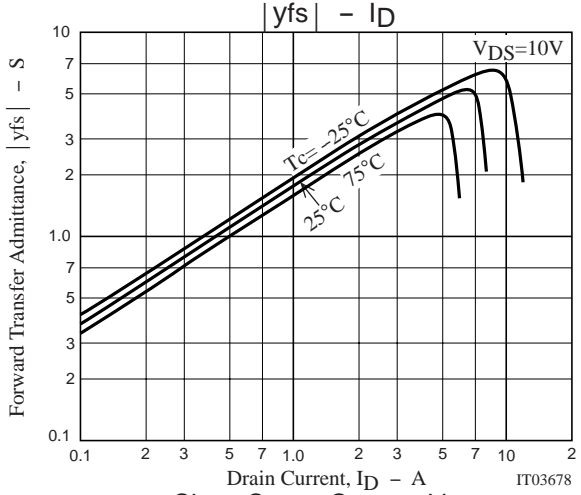
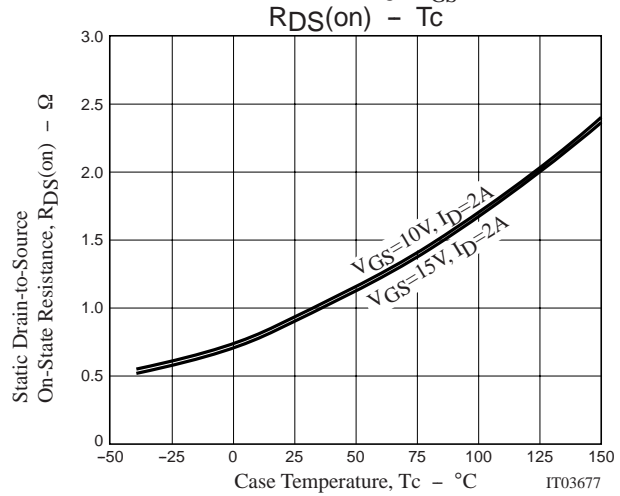
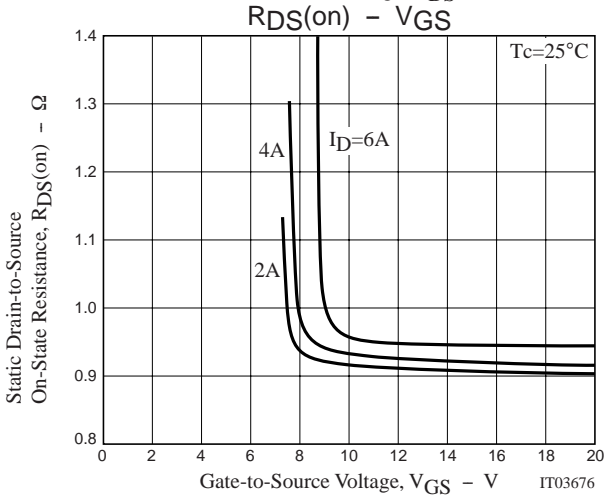
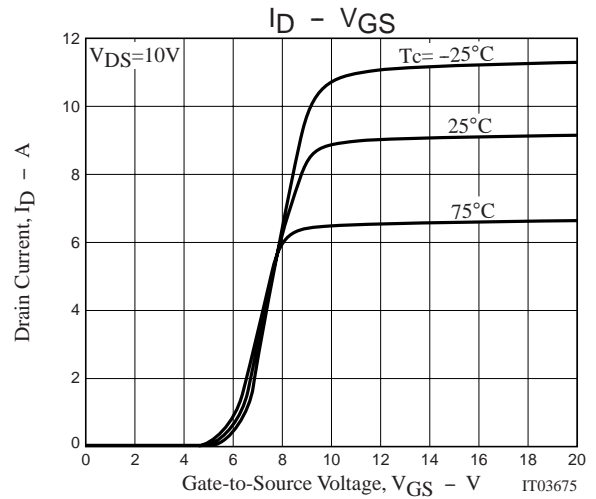
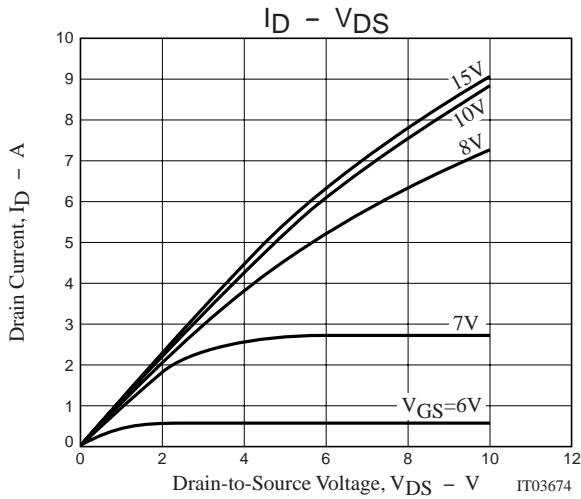


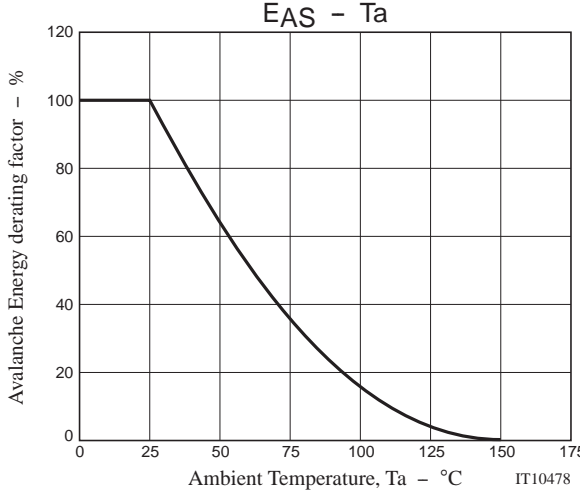
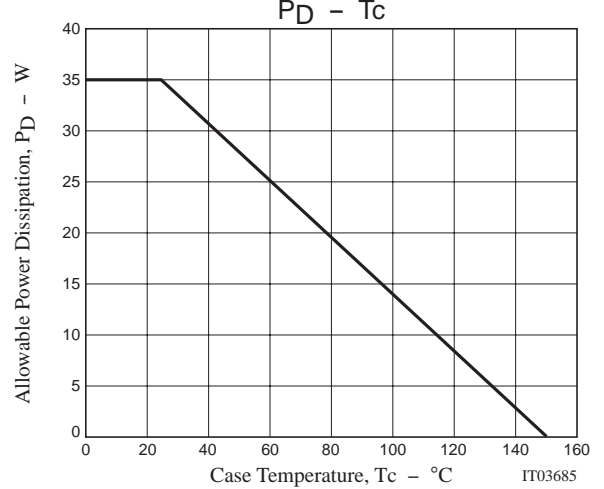
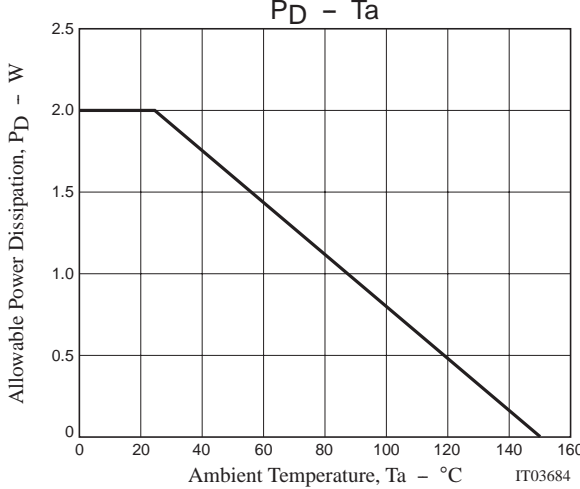
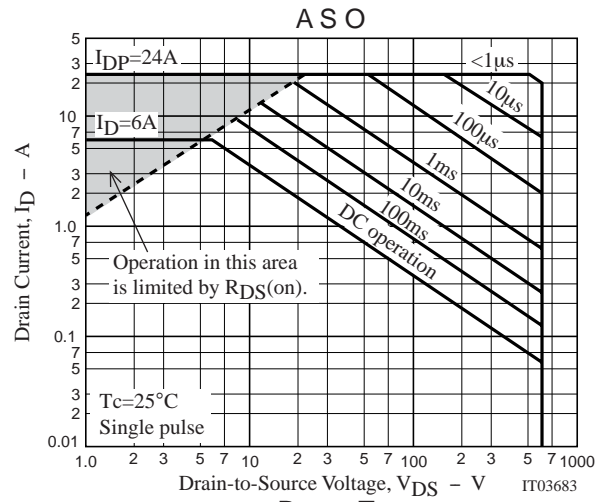
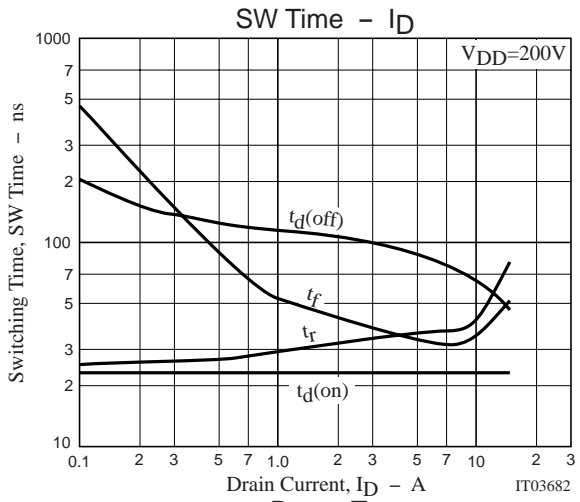
**Switching Time Test Circuit**



**Avalanche Resistance Test Circuit**







Note on usage : Since the 2SK2628LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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